PHOTOTRANSISTOR

BPW 40

Features

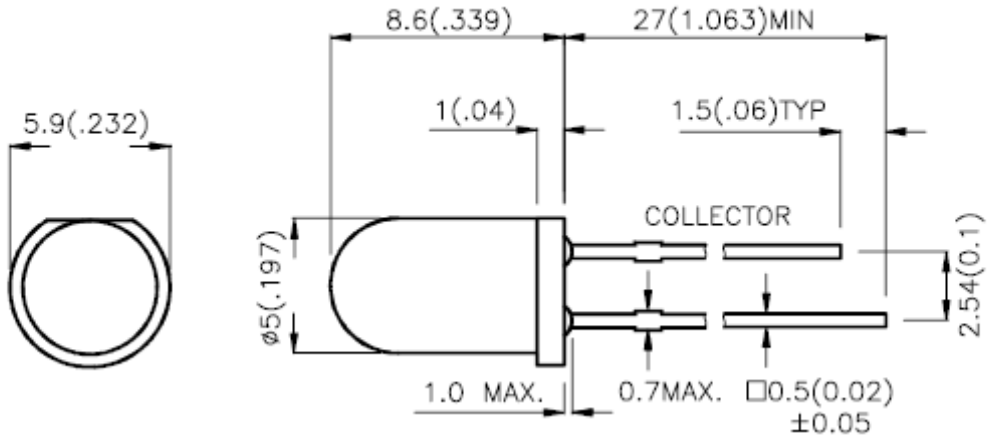
● MECHANICALLY AND SPECTRALLY MATCHED TO THE BPW 40 INFRARED EMITTING LED LAMP.

●WATER CLEAR LENS

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All Dimensions are in millimeters (inches).
2. Tolerance is ± 0.25 (0.01") unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Electrical / Optical Characteristics at T_A=25°C

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condiction
$V_{BR\ CEO}$	Collector-to-Emitter Breakdown Voltage	30	-	-	V	I_C=100uA E_e=0mW/cm²
$V_{BR\ ECO}$	Emitter-to-Collector Breakdown Voltage	5	-	-	V	I_E=100uA E_e=0mW/cm²
$V_{CE\ (SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	I_C=2mA E_e=20mW/cm²
I_{CEO}	Collector Dark Current	-	-	100	nA	V_{CE}=10V E_e=0mW/cm²
T_R	Rise Time (10% to 90%)	-	3	-	us	V_{CE}=5V I_C=1mA R_L=1000Ω
T_F	Fall Time (90% to 10%)	-	3	-	us	
$I_{(ON)}$	On State Collector Current	0.1	0.5	-	mA	V_{CE}=5V E_e=1mW/cm² λ=940nm

Absolute Maximum Ratings at T_A=25°C

Parameter	Maximum Rating
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	-40°C ~ +85°C
Storage Temperature Range	-40°C ~ +85°C
Lead soldering Temperature (>5mm for 5sec)	260°C